

or the like, thereby to restrict adsorption of metal into the wafer surface. --.

Please delete the paragraph at page 7, lines 8-17, and substitute therefor the following new paragraph:

A3 -- According to a second aspect of the present invention, there is provided a method of manufacturing a semiconductor integrated circuit device, comprising steps of (a) cleaning a surface of a silicon wafer with use of a processing solution containing hydrogen peroxide, hydroacid fluoride salt, and water, (b) subjecting the silicon wafer to a heat treatment thereby to form a gate oxide film on the surface of the silicon wafer, and (c) patterning a conductive film deposited above the gate oxide film, thereby to form a gate electrode. --.

Please delete the heading at page 10, line 17, and substitute therefor the following new heading:

A4 -- DESCRIPTION OF THE PREFERRED EMBODIMENTS --.

Please delete the paragraph on page 13, lines 7-17, and substitute therefor the following new paragraph:

A5 -- Next, as shown in FIG. 4, a silicon oxide film 7 having a film thickness of about 800 nm is deposited, for example, by a CVD method using oxygen and tetraethoxysilane as a source gas. Thereafter, as shown in FIG. 5, the silicon oxide film 7 is polished by a Chemical Mechanical Polishing (CMP) method. As the silicon oxide film 7 remains only inside

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cont

the groove 5a with using the silicon nitride film 3 as a polishing stopper, an element separation 5 is formed.

Subsequently, a heat treatment at about 1000 °C is carried out to densify (sinter) the silicon oxide film 7 in the element separation groove 5. --.

Please delete the paragraph bridging pages 15 and 16, and substitute therefor the following new paragraph:

A6

-- The wafers 1 which have been loaded to the loader 101 of the cleaning/oxide-film-forming device 100 are transferred to the cleaning chamber 102, in units of every one or two sheet, and are dipped into a processing solution composed of a hydrogen peroxide, a hydracid salt fluoride and water. Here, the hydracid salt fluoride is, for example, tetraalkyl ammonium fluoride such as tetramethyl ammonium fluoride, tetraethyl ammonium fluoride, or ammonium fluoride. --.

Please delete the paragraph on page 22, lines 15-22, and substitute therefor the following new paragraph:

A7

-- The strong alkaline component is, for example, tetraalkyl ammonium hydroxide such as tetramethyl ammonium hydroxide, tetraethyl ammonium hydroxide, or the like. Amine may be used instead of ammonium. The amine is, for example, primary amine such as monomethyl amine or monoethyl amine, secondary amine such as dimethyl amine or diethyl amine, or tertiary amine such as trimethyl amine or triethyl amine. --.